

## ABSTRACT OF THE DISCLOSURE

A semiconductor laser device has an n-GaAs substrate (1). On the n-GaAs substrate (1), by turns, an n-AlGaInP clad layer (2), an AlGaInP/GaInP MQW active layer (3), a p-AlGaInP first clad layer (4), a p-Al<sub>x</sub>Ga<sub>1-x</sub>As-ESL (5) of a single layer, a p-AlGaInP second clad layer (7) with a stripe-form protrusion (6), and a p-GaAs contact layer (8) are provided. The portion other than the stripe-form protrusion (6) of the p-AlGaInP second clad layer (7) is covered with an insulative film (9). The refractive index of the p-Al<sub>x</sub>Ga<sub>1-x</sub>As-ESL (5) is nearly equal to the refractive index of each of the clad layers (2), (4) and (7).